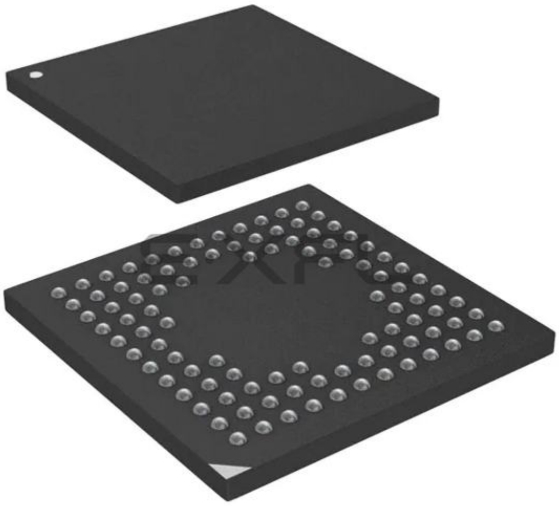
STMicroelectronics - STM32L462VEI6 Datasheet



Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, PWM, WDT
Number of I/O	83
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	160K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-UFBGA
Supplier Device Package	100-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l462vei6

List of tables

By default, the microcontroller is in Run mode after a system or a power Reset. It is up to the user to select one of the low-power modes described below:

- **Sleep** mode

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.
- **Low-power run** mode

  This mode is achieved with V_{CORE} supplied by the low-power regulator to minimize the regulator's operating current. The code can be executed from SRAM or from Flash, and the CPU frequency is limited to 2 MHz. The peripherals with independent clock can be clocked by HSI16.
- **Low-power sleep** mode

  This mode is entered from the low-power run mode. Only the CPU clock is stopped. When wakeup is triggered by an event or an interrupt, the system reverts to the low-power run mode.
- **Stop 0, Stop 1 and Stop 2** modes

  Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the V_{CORE} domain are stopped, the PLL, the MSI RC, the HSI16 RC and the HSE crystal oscillators are disabled. The LSE or LSI is still running.

  The RTC can remain active (Stop mode with RTC, Stop mode without RTC).

  Some peripherals with wakeup capability can enable the HSI16 RC during Stop mode to detect their wakeup condition.

  Three Stop modes are available: Stop 0, Stop 1 and Stop 2 modes. In Stop 2 mode, most of the V_{CORE} domain is put in a lower leakage mode.

  Stop 1 offers the largest number of active peripherals and wakeup sources, a smaller wakeup time but a higher consumption than Stop 2. In Stop 0 mode, the main regulator remains ON, allowing a very fast wakeup time but with much higher consumption.

  The system clock when exiting from Stop 0, Stop 1 or Stop 2 modes can be either MSI up to 48 MHz or HSI16, depending on software configuration.
- **Standby** mode

  The Standby mode is used to achieve the lowest power consumption with BOR. The internal regulator is switched off so that the V_{CORE} domain is powered off. The PLL, the MSI RC, the HSI16 RC and the HSE crystal oscillators are also switched off.

  The RTC can remain active (Standby mode with RTC, Standby mode without RTC).

  The brown-out reset (BOR) always remains active in Standby mode.

  The state of each I/O during standby mode can be selected by software: I/O with internal pull-up, internal pull-down or floating.

  After entering Standby mode, SRAM1 and register contents are lost except for registers in the Backup domain and Standby circuitry. Optionally, SRAM2 can be retained in Standby mode, supplied by the low-power Regulator (Standby with SRAM2 retention mode).

  The device exits Standby mode when an external reset (NRST pin), an IWDG reset, WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper) or a failure is detected on LSE (CSS on LSE).

  The system clock after wakeup is MSI up to 8 MHz.

The main features of the touch sensing controller are the following:

- Proven and robust surface charge transfer acquisition principle
- Supports up to 21 capacitive sensing channels
- Up to 3 capacitive sensing channels can be acquired in parallel offering a very good response time
- Spread spectrum feature to improve system robustness in noisy environments
- Full hardware management of the charge transfer acquisition sequence
- Programmable charge transfer frequency
- Programmable sampling capacitor I/O pin
- Programmable channel I/O pin
- Programmable max count value to avoid long acquisition when a channel is faulty
- Dedicated end of acquisition and max count error flags with interrupt capability
- One sampling capacitor for up to 3 capacitive sensing channels to reduce the system components
- Compatible with proximity, touchkey, linear and rotary touch sensor implementation
- Designed to operate with STMTouch touch sensing firmware library

Note: The number of capacitive sensing channels is dependent on the size of the packages and subject to I/O availability.

3.21 Digital filter for Sigma-Delta Modulators (DFSDM)

The device embeds one DFSDM with 2 digital filters modules and 4 external input serial channels (transceivers) or alternately 4 internal parallel inputs support.

The DFSDM peripheral is dedicated to interface the external ΣΔ modulators to microcontroller and then to perform digital filtering of the received data streams (which represent analog value on ΣΔ modulators inputs). DFSDM can also interface PDM (Pulse Density Modulation) microphones and perform PDM to PCM conversion and filtering in

3.26 Inter-integrated circuit interface (I^2C)

The device embeds four I2C. Refer to *Table 11: I2C implementation* for the features implementation.

The I^2C bus interface handles communications between the microcontroller and the serial I^2C bus. It controls all I^2C bus-specific sequencing, protocol, arbitration and timing.

The I2C peripheral supports:

- I^2C-bus specification and user manual rev. 5 compatibility:
  - Slave and master modes, multimaster capability
  - Standard-mode (Sm), with a bitrate up to 100 kbit/s
  - Fast-mode (Fm), with a bitrate up to 400 kbit/s
  - Fast-mode Plus (Fm+), with a bitrate up to 1 Mbit/s and 20 mA output drive I/Os
  - 7-bit and 10-bit addressing mode, multiple 7-bit slave addresses
  - Programmable setup and hold times
  - Optional clock stretching
- System Management Bus (SMBus) specification rev 2.0 compatibility:
  - Hardware PEC (Packet Error Checking) generation and verification with ACK control
  - Address resolution protocol (ARP) support
  - SMBus alert
- Power System Management Protocol (PMBus^{TM}) specification rev 1.1 compatibility
- Independent clock: a choice of independent clock sources allowing the I2C communication speed to be independent from the PCLK reprogramming. Refer to *Figure 4: Clock tree*.
- Wakeup from Stop mode on address match
- Programmable analog and digital noise filters
- 1-byte buffer with DMA capability

Table 11. I2C implementation

I2C features[1]	I2C1	I2C2	I2C3	I2C4
Standard-mode (up to 100 kbit/s)	X	X	X	X
Fast-mode (up to 400 kbit/s)	X	X	X	X
Fast-mode Plus with 20mA output drive I/Os (up to 1 Mbit/s)	X	X	X	X
Programmable analog and digital noise filters	X	X	X	X
SMBus/PMBus hardware support	X	X	X	X
Independent clock	X	X	X	X
Wakeup from Stop 1 mode on address match	X	X	X	X
Wakeup from Stop 2 mode on address match	-	-	X	-

1. X: supported

2. The related I/O structures in *Table 15* are: FT_u, FT_fu.
3. The related I/O structures in *Table 15* are: FT_a, FT_fa, TT_a.

Table 15. STM32L462xx pin definitions

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
UFQFPN48	WLCSP64	LQFP64	UFBGA64	LQFP100	UFBGA100					Alternate functions	Additional functions
-	-	-	-	1	B2	PE2	I/O	FT	-	TRACECK, TIM3_ETR, TSC_G7_IO1, SAI1_MCLK_A, EVENTOUT	-
-	-	-	-	2	A1	PE3	I/O	FT	-	TRACED0, TIM3_CH1, TSC_G7_IO2, SAI1_SD_B, EVENTOUT	-
-	-	-	-	3	B1	PE4	I/O	FT	-	TRACED1, TIM3_CH2, DFSDM1_DATIN3, TSC_G7_IO3, SAI1_FS_A, EVENTOUT	-
-	-	-	-	4	C2	PE5	I/O	FT	-	TRACED2, TIM3_CH3, DFSDM1_CKIN3, TSC_G7_IO4, SAI1_SCK_A, EVENTOUT	-
-	-	-	-	5	D2	PE6	I/O	FT	-	TRACED3, TIM3_CH4, SAI1_SD_A, EVENTOUT	RTC_TAMP3, WKUP3
1	B7	1	B2	6	E2	VBAT	S	-	-	-	-
2	B8	2	A2	7	C1	PC13	I/O	FT	(1) (2)	EVENTOUT	RTC_TAMP1, RTC_TS, RTC_OUT, WKUP2
3	C8	3	A1	8	D1	PC14-OSC32_IN (PC14)	I/O	FT	(1) (2)	EVENTOUT	OSC32_IN
4	C7	4	B1	9	E1	PC15-OSC32_OUT (PC15)	I/O	FT	(1) (2)	EVENTOUT	OSC32_OUT
-	-	-	-	10	F2	VSS	S	-	-	-	-
-	-	-	-	11	G2	VDD	S	-	-	-	-
5	D8	5	C1	12	F1	PH0-OSC_IN (PH0)	I/O	FT	-	EVENTOUT	OSC_IN
6	E8	6	D1	13	G1	PH1-OSC_OUT (PH1)	I/O	FT	-	EVENTOUT	OSC_OUT

Table 15. STM32L462xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
UFQFPN48	WLCSP64	LQFP64	UFBGA64	LQFP100	UFBGA100					Alternate functions	Additional functions
-	C4	54	B5	83	C8	PD2	I/O	FT	-	TRACED2, TIM3_ETR, USART3_RTS_DE, TSC_SYNC, SDMMC1_CMD, EVENTOUT	-
-	-	-	-	84	B8	PD3	I/O	FT	-	SPI2_MISO, DFSDM1_DATIN0, USART2_CTS, QUADSPI_BK2_NCS, EVENTOUT	-
-	-	-	-	85	B7	PD4	I/O	FT	-	SPI2_MOSI, DFSDM1_CKIN0, USART2_RTS_DE, QUADSPI_BK2_IO0, EVENTOUT	-
-	-	-	-	86	A6	PD5	I/O	FT	-	USART2_TX, QUADSPI_BK2_IO1, EVENTOUT	-
-	-	-	-	87	B6	PD6	I/O	FT	-	DFSDM1_DATIN1, USART2_RX, QUADSPI_BK2_IO2, SAI1_SD_A, EVENTOUT	-
-	-	-	-	88	A5	PD7	I/O	FT	-	DFSDM1_CKIN1, USART2_CK, QUADSPI_BK2_IO3, EVENTOUT	-
39	B4	55	A5	89	A8	PB3 (JTDO/ TRACESWO)	I/O	FT_a	(3)	JTDO/TRACESWO, TIM2_CH2, SPI1_SCK, SPI3_SCK, USART1_RTS_DE, SAI1_SCK_B, EVENTOUT	COMP2_INM
40	A4	56	A4	90	A7	PB4 (NJTRST)	I/O	FT_fa	(3)	NJTRST, TIM3_CH1, I2C3_SDA, SPI1_MISO, SPI3_MISO, USART1_CTS, TSC_G2_IO1, SAI1_MCLK_B, EVENTOUT	COMP2_INP

Table 18. STM32L462xx memory map and peripheral register boundary addresses(1) (continued)

Bus	Boundary address	Size(bytes)	Peripheral
APB1	0x4000 9800 - 0x4000 FFFF	26 KB	Reserved
	0x4000 9400 - 0x4000 97FF	1 KB	LPTIM2
	0x4000 8800 - 0x4000 93FF	3 KB	Reserved
	0x4000 8400 - 0x4000 87FF	1 KB	I2C4
	0x4000 8000 - 0x4000 83FF	1 KB	LPUART1
	0x4000 7C00 - 0x4000 7FFF	1 KB	LPTIM1
	0x4000 7800 - 0x4000 7BFF	1 KB	OPAMP
	0x4000 7400 - 0x4000 77FF	1 KB	DAC1
	0x4000 7000 - 0x4000 73FF	1 KB	PWR
	0x4000 6C00 - 0x4000 6FFF	1 KB	USB SRAM
	0x4000 6800 - 0x4000 6BFF	1 KB	USB FS
	0x4000 6400 - 0x4000 67FF	1 KB	CAN1
	0x4000 6000 - 0x4000 63FF	1 KB	CRS
	0x4000 5C00- 0x4000 5FFF	1 KB	I2C3
	0x4000 5800 - 0x4000 5BFF	1 KB	I2C2
	0x4000 5400 - 0x4000 57FF	1 KB	I2C1
	0x4000 5000 - 0x4000 53FF	1 KB	Reserved
	0x4000 4C00 - 0x4000 4FFF	1 KB	UART4
	0x4000 4800 - 0x4000 4BFF	1 KB	USART3
	0x4000 4400 - 0x4000 47FF	1 KB	USART2
	0x4000 4000 - 0x4000 43FF	1 KB	Reserved
	0x4000 3C00 - 0x4000 3FFF	1 KB	SPI3
	0x4000 3800 - 0x4000 3BFF	1 KB	SPI2
	0x4000 3400 - 0x4000 37FF	1 KB	Reserved
	0x4000 3000 - 0x4000 33FF	1 KB	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 KB	WWDG
APB1	0x4000 2800 - 0x4000 2BFF	1 KB	RTC
	0x4000 1400 - 0x4000 27FF	5 KB	Reserved
	0x4000 1000 - 0x4000 13FF	1 KB	TIM6
	0x4000 0800- 0x4000 0FFF	2 KB	Reserved
	0x4000 0400 - 0x4000 07FF	1 KB	TIM3
	0x4000 0000 - 0x4000 03FF	1 KB	TIM2

1. The gray color is used for reserved boundary addresses.

Table 30. Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART disable

Symbol	Parameter	Conditions			TYP	Unit	TYP	Unit
		-	Voltage scaling	Code	25 °C		25 °C	
I_{DD_ALL} (Run)	Supply current in Run mode	f_{HCLK} = f_{HSE} up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2 f_{HCLK} = 26 MHz	Reduced code(1)	2.75	mA	106	µA/MHz
				Coremark	2.50		96	
				Dhrystone 2.1	2.50		96	
				Fibonacci	2.30		88	
				While(1)	2.20		84.6	
			Range 1 f_{HCLK} = 80 MHz	Reduced code(1)	8.85	mA	111	µA/MHz
				Coremark	8.15		102	
				Dhrystone 2.1	8.15		102	
				Fibonacci	7.55		94	
				While(1)	7.95		99	
I_{DD_ALL} (LPRun)	Supply current in Low-power run	f_{HCLK} = f_{MSI} = 2 MHz all peripherals disable		Reduced code(1)	340	µA	170	µA/MHz
				Coremark	380		190	
				Dhrystone 2.1	355		178	
				Fibonacci	355		178	
				While(1)	405		203	

1. Reduced code used for characterization results provided in *Table 26*, *Table 27*, *Table 28*.

Table 31. Typical current consumption in Run and Low-power run modes, with different codes running from SRAM1

Symbol	Parameter	Conditions			TYP	Unit	TYP	Unit
		-	Voltage scaling	Code	25 °C		25 °C	
I_{DD_ALL} (Run)	Supply current in Run mode	f_{HCLK} = f_{HSE} up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2 f_{HCLK} = 26 MHz	Reduced code(1)	2.40	mA	92	µA/MHz
				Coremark	2.20		85	
				Dhrystone 2.1	2.35		90	
				Fibonacci	2.20		85	
				While(1)	2.30		88	
			Range 1 f_{HCLK} = 80 MHz	Reduced code(1)	8.55	mA	107	µA/MHz
				Coremark	7.75		97	
				Dhrystone 2.1	8.45		106	
				Fibonacci	7.80		98	
				While(1)	8.75		109	
I_{DD_ALL} (LPRun)	Supply current in Low-power run	f_{HCLK} = f_{MSI} = 2 MHz all peripherals disable		Reduced code(1)	220	µA	110	µA/MHz
				Coremark	190		95	
				Dhrystone 2.1	215		108	
				Fibonacci	200		100	
				While(1)	210		105	

1. Reduced code used for characterization results provided in *Table 26*, *Table 27*, *Table 28*.

Table 32. Current consumption in Sleep and Low-power sleep modes, Flash ON

Symbol	Parameter	Conditions			TYP					MAX[1]					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (Sleep)	Supply current in sleep mode,	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode pll ON above 48 MHz all peripherals disable	Range 2	26 MHz	0.700	0.730	0.830	1.00	1.35	0.80	0.90	1.05	1.30	1.90	mA
				16 MHz	0.475	0.505	0.605	0.775	1.10	0.55	0.65	0.80	1.05	1.65	
				8 MHz	0.300	0.325	0.425	0.590	0.920	0.35	0.45	0.60	0.85	1.45	
				4 MHz	0.210	0.235	0.335	0.500	0.830	0.25	0.30	0.45	0.75	1.35	
				2 MHz	0.165	0.190	0.290	0.455	0.785	0.20	0.25	0.40	0.70	1.25	
				1 MHz	0.145	0.170	0.265	0.430	0.760	0.15	0.25	0.40	0.65	1.25	
				100 kHz	0.125	0.150	0.245	0.410	0.740	0.15	0.20	0.35	0.65	1.20	
			Range 1	80 MHz	2.30	2.35	2.45	2.65	3.05	2.55	2.65	2.85	3.15	3.80	
				72 MHz	2.10	2.15	2.25	2.45	2.80	2.35	2.40	2.60	2.90	3.55	
				64 MHz	1.90	1.90	2.05	2.25	2.60	2.10	2.20	2.35	2.70	3.35	
				48 MHz	1.40	1.40	1.55	1.75	2.15	1.60	1.65	1.85	2.15	2.80	
				32 MHz	0.970	1.00	1.15	1.30	1.70	1.10	1.20	1.40	1.70	2.35	
				24 MHz	0.765	0.800	0.920	1.10	1.50	0.90	0.95	1.15	1.45	2.10	
				16 MHz	0.555	0.590	0.705	0.895	1.25	0.65	0.75	0.90	1.20	1.85	
I_{DD_ALL} (LPSleep)	Supply current in low-power sleep mode	$f_{HCLK} = f_{MSI}$ all peripherals disable		2 MHz	76.0	110	215	395	745	120	185	355	610	1250	µA
				1 MHz	54.0	86.5	195	370	725	88.5	160	335	585	1250	
				400 kHz	39.0	70.5	175	355	710	68.5	140	320	570	1200	
				100 kHz	35.5	75.0	195	345	715	66.0	130	305	560	1200	

1. Guaranteed by characterization results, unless otherwise specified.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 60: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 40: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load
V_{DDIOx} is the I/O supply voltage
f_{SW} is the I/O switching frequency
C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$
C_S is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Table 40. Peripheral current consumption (continued)

Peripheral		Range 1	Range 2	Low-power run and sleep	Unit
APB1	DAC1	2.4	1.8	2.2	µA/MHz
	RTCA	1.7	1.1	2.1	
	CRS	0.3	0.3	0.6	
	USB FS independent clock domain	2.9	N/A	N/A	
	USB FS clock domain	2.3	N/A	N/A	
	I2C1 independent clock domain	3.5	2.8	3.4	
	I2C1 clock domain	1.1	0.9	1.0	
	I2C2 independent clock domain	3.5	3.0	3.4	
	I2C2 clock domain	1.1	0.7	0.9	
	I2C3 independent clock domain	2.9	2.3	2.5	
	I2C3 clock domain	0.9	0.4	0.8	
	LPUART1 independent clock domain	1.9	1.6	1.8	
	LPUART1 clock domain	0.6	0.6	0.6	
	LPTIM1 independent clock domain	2.9	2.4	2.8	
	LPTIM1 clock domain	0.8	0.4	0.7	
	LPTIM2 independent clock domain	3.1	2.7	3.9	
	LPTIM2 clock domain	0.8	0.7	0.8	
	OPAMP	0.4	0.2	0.4	
	PWR	0.4	0.1	0.4	
	SPI2	1.8	1.6	1.6	
	SPI3	1.7	1.3	1.6	
	TIM2	6.2	5.0	5.9	
	TIM6	1.0	0.6	0.9	
	USART2 independent clock domain	4.1	3.6	3.8	
	USART2 clock domain	1.3	0.9	1.1	
	USART3 independent clock domain	4.3	3.5	4.2	
	USART3 clock domain	1.5	1.1	1.3	
	WWDG	0.5	0.5	0.5	
	All APB1 on	51.5	35.5	48.6	

Table 49. MSI oscillator characteristics(1) (continued)

Symbol	Parameter	Conditions			Min	Typ	Max	Unit
I_{DD}(MSI)(6)	MSI oscillator power consumption	MSI and PLL mode	Range 0	-	-	0.6	1	µA
			Range 1	-	-	0.8	1.2	
			Range 2	-	-	1.2	1.7	
			Range 3	-	-	1.9	2.5	
			Range 4	-	-	4.7	6	
			Range 5	-	-	6.5	9	
			Range 6	-	-	11	15	
			Range 7	-	-	18.5	25	
			Range 8	-	-	62	80	
			Range 9	-	-	85	110	
			Range 10	-	-	110	130	
			Range 11	-	-	155	190	

1. Guaranteed by characterization results.
2. This is a deviation for an individual part once the initial frequency has been measured.
3. Sampling mode means Low-power run/Low-power sleep modes with Temperature sensor disable.
4. Average period of MSI @48 MHz is compared to a real 48 MHz clock over 28 cycles. It includes frequency tolerance + jitter of MSI @48 MHz clock.
5. Only accumulated jitter of MSI @48 MHz is extracted over 28 cycles.
   For next transition: min. and max. jitter of 2 consecutive frame of 28 cycles of the MSI @48 MHz, for 1000 captures over 28 cycles.
   For paired transitions: min. and max. jitter of 2 consecutive frame of 56 cycles of the MSI @48 MHz, for 1000 captures over 56 cycles.
6. Guaranteed by design.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 56. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8 MHz/ 80 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 MHz to 30 MHz	-8	dBµV
			30 MHz to 130 MHz	2	
			130 MHz to 1 GHz	5	
			1 GHz to 2 GHz	8	
			EMI Level	2.5	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 57. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value[1]	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to ANSI/ESDA/JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	C3	250	

1. Guaranteed by characterization results.

Table 68. ADC accuracy - limited test conditions 1[(1)(2)(3)]

Sym-bol	Parameter	Conditions[(4)]			Min	Typ	Max	Unit
ET	Total unadjusted error	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, V_{DDA} = VREF+ = 3 V, TA = 25 °C	Single ended	Fast channel (max speed)	-	4	5	LSB
				Slow channel (max speed)	-	4	5	
			Differential	Fast channel (max speed)	-	3.5	4.5	
				Slow channel (max speed)	-	3.5	4.5	
EO	Offset error		Single ended	Fast channel (max speed)	-	1	2.5	
				Slow channel (max speed)	-	1	2.5	
			Differential	Fast channel (max speed)	-	1.5	2.5	
				Slow channel (max speed)	-	1.5	2.5	
EG	Gain error		Single ended	Fast channel (max speed)	-	2.5	4.5	
				Slow channel (max speed)	-	2.5	4.5	
			Differential	Fast channel (max speed)	-	2.5	3.5	
				Slow channel (max speed)	-	2.5	3.5	
ED	Differential linearity error		Single ended	Fast channel (max speed)	-	1	1.5	
				Slow channel (max speed)	-	1	1.5	
			Differential	Fast channel (max speed)	-	1	1.2	
				Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error		Single ended	Fast channel (max speed)	-	1.5	2.5	
				Slow channel (max speed)	-	1.5	2.5	
			Differential	Fast channel (max speed)	-	1	2	
				Slow channel (max speed)	-	1	2	
ENOB	Effective number of bits		Single ended	Fast channel (max speed)	10.4	10.5	-	bits
				Slow channel (max speed)	10.4	10.5	-	
			Differential	Fast channel (max speed)	10.8	10.9	-	
				Slow channel (max speed)	10.8	10.9	-	
SINAD	Signal-to-noise and distortion ratio		Single ended	Fast channel (max speed)	64.4	65	-	dB
				Slow channel (max speed)	64.4	65	-	
			Differential	Fast channel (max speed)	66.8	67.4	-	
				Slow channel (max speed)	66.8	67.4	-	
SNR	Signal-to-noise ratio		Single ended	Fast channel (max speed)	65	66	-	
				Slow channel (max speed)	65	66	-	
			Differential	Fast channel (max speed)	67	68	-	
				Slow channel (max speed)	67	68	-	

Table 69. ADC accuracy - limited test conditions 2(1)(2)(3) (continued)

Sym-bol	Parameter	Conditions(4)			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, 2 V ≤ V_{DDA}	Single ended	Fast channel (max speed)	-	-74	-65	dB
				Slow channel (max speed)	-	-74	-67	
			Differential	Fast channel (max speed)	-	-79	-70	
				Slow channel (max speed)	-	-79	-71	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4 V). It is disable when V_{DDA} ≥ 2.4 V. No oversampling.

Table 71. ADC accuracy - limited test conditions 4[(1)(2)(3)]

Sym-bol	Parameter	Conditions(4)			Min	Typ	Max	Unit
ET	Total unadjusted error	ADC clock frequency ≤ 26 MHz, 1.65 V ≤ V_{DDA} = VREF+ ≤ 3.6 V, Voltage scaling Range 2	Single ended	Fast channel (max speed)	-	5	5.4	LSB
				Slow channel (max speed)	-	4	5	
			Differential	Fast channel (max speed)	-	4	5	
				Slow channel (max speed)	-	3.5	4.5	
EO	Offset error		Single ended	Fast channel (max speed)	-	2	4	
				Slow channel (max speed)	-	2	4	
			Differential	Fast channel (max speed)	-	2	3.5	
				Slow channel (max speed)	-	2	3.5	
EG	Gain error		Single ended	Fast channel (max speed)	-	4	4.5	
				Slow channel (max speed)	-	4	4.5	
			Differential	Fast channel (max speed)	-	3	4	
				Slow channel (max speed)	-	3	4	
ED	Differential linearity error		Single ended	Fast channel (max speed)	-	1	1.5	
				Slow channel (max speed)	-	1	1.5	
			Differential	Fast channel (max speed)	-	1	1.2	
				Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error		Single ended	Fast channel (max speed)	-	2.5	3	
				Slow channel (max speed)	-	2.5	3	
			Differential	Fast channel (max speed)	-	2	2.5	
				Slow channel (max speed)	-	2	2.5	
ENOB	Effective number of bits		Single ended	Fast channel (max speed)	10.2	10.5	-	bits
				Slow channel (max speed)	10.2	10.5	-	
			Differential	Fast channel (max speed)	10.6	10.7	-	
				Slow channel (max speed)	10.6	10.7	-	
SINAD	Signal-to-noise and distortion ratio		Single ended	Fast channel (max speed)	63	65	-	dB
				Slow channel (max speed)	63	65	-	
			Differential	Fast channel (max speed)	65	66	-	
				Slow channel (max speed)	65	66	-	
SNR	Signal-to-noise ratio		Single ended	Fast channel (max speed)	64	65	-	
				Slow channel (max speed)	64	65	-	
			Differential	Fast channel (max speed)	66	67	-	
				Slow channel (max speed)	66	67	-	

Table 87. SAI characteristics[1] (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{v(SD\_B\_ST)}$	Data output valid time	Slave transmitter (after enable edge) $2.7 \leq V_{DD} \leq 3.6$	-	22	ns
		Slave transmitter (after enable edge) $1.71 \leq V_{DD} \leq 3.6$	-	34	
$t_{h(SD\_B\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	10	-	ns
$t_{v(SD\_A\_MT)}$	Data output valid time	Master transmitter (after enable edge) $2.7 \leq V_{DD} \leq 3.6$	-	27	ns
		Master transmitter (after enable edge) $1.71 \leq V_{DD} \leq 3.6$	-	40	
$t_{h(SD\_A\_MT)}$	Data output hold time	Master transmitter (after enable edge)	10	-	ns

1. Guaranteed by characterization results.
2. APB clock frequency must be at least twice SAI clock frequency.

Figure 36. SAI master timing waveforms

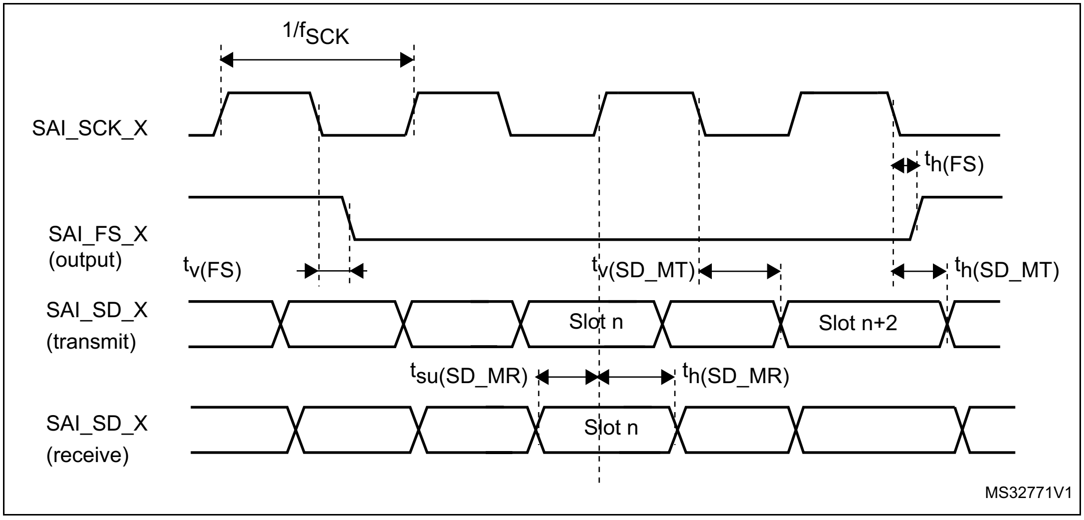


Table 88. SD / MMC dynamic characteristics, V_{DD}=2.7 V to 3.6 V(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
CMD, D outputs (referenced to CK) in SD default mode						
t_{OVD}	Output valid default time SD	f_{PP} = 50 MHz	-	2	3	ns
t_{OHD}	Output hold default time SD	f_{PP} = 50 MHz	0	-	-	ns

1. Guaranteed by characterization results.

Table 89. eMMC dynamic characteristics, V_{DD} = 1.71 V to 1.9 V(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/f_{PCLK2} frequency ratio	-	-	-	4/3	-
$t_{W(CKL)}$	Clock low time	f_{PP} = 50 MHz	8	10	-	ns
$t_{W(CKH)}$	Clock high time	f_{PP} = 50 MHz	8	10	-	ns
CMD, D inputs (referenced to CK) in eMMC mode						
t_{ISU}	Input setup time HS	f_{PP} = 50 MHz	0	-	-	ns
t_{IH}	Input hold time HS	f_{PP} = 50 MHz	1.5	-	-	ns
CMD, D outputs (referenced to CK) in eMMC mode						
t_{OV}	Output valid time HS	f_{PP} = 50 MHz	-	13.5	15	ns
t_{OH}	Output hold time HS	f_{PP} = 50 MHz	9	-	-	ns

1. Guaranteed by characterization results.
2. C_{LOAD} = 20pF.

Figure 38. SDIO high-speed mode

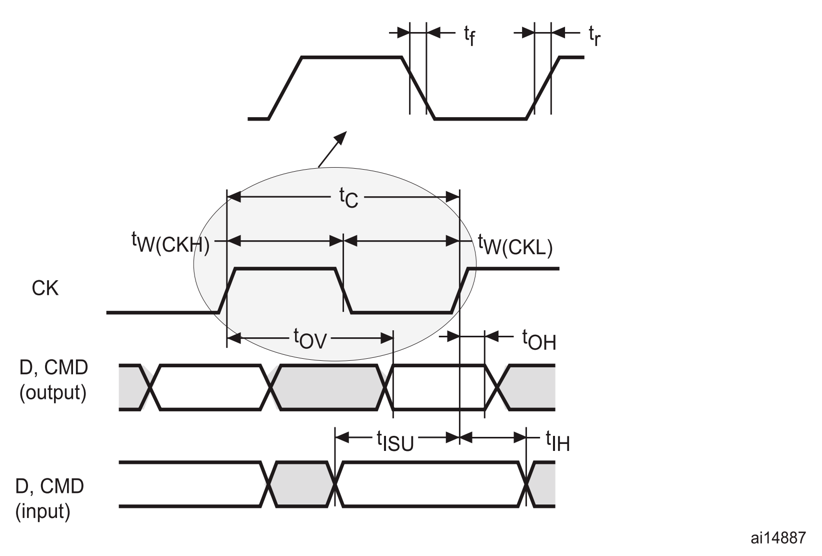
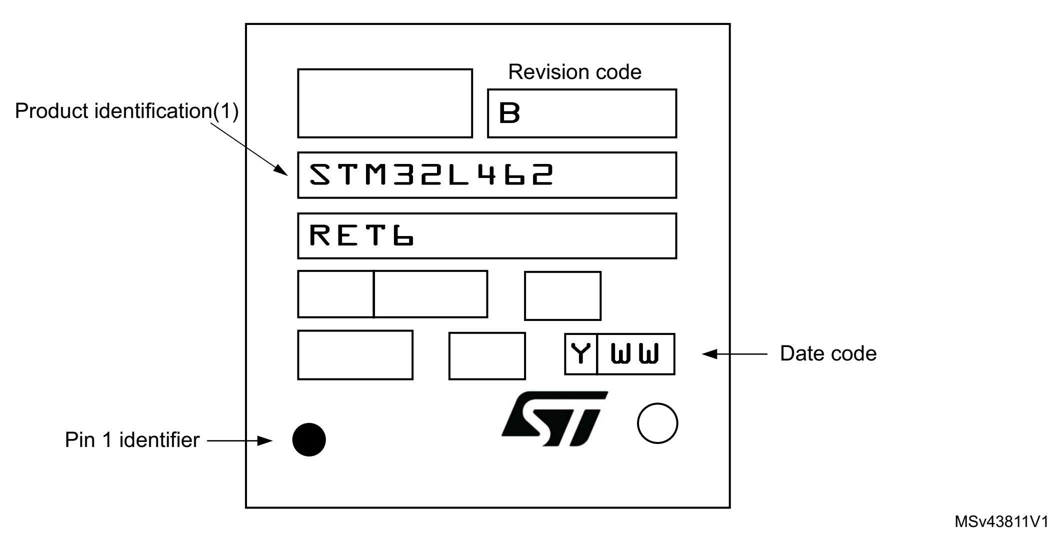


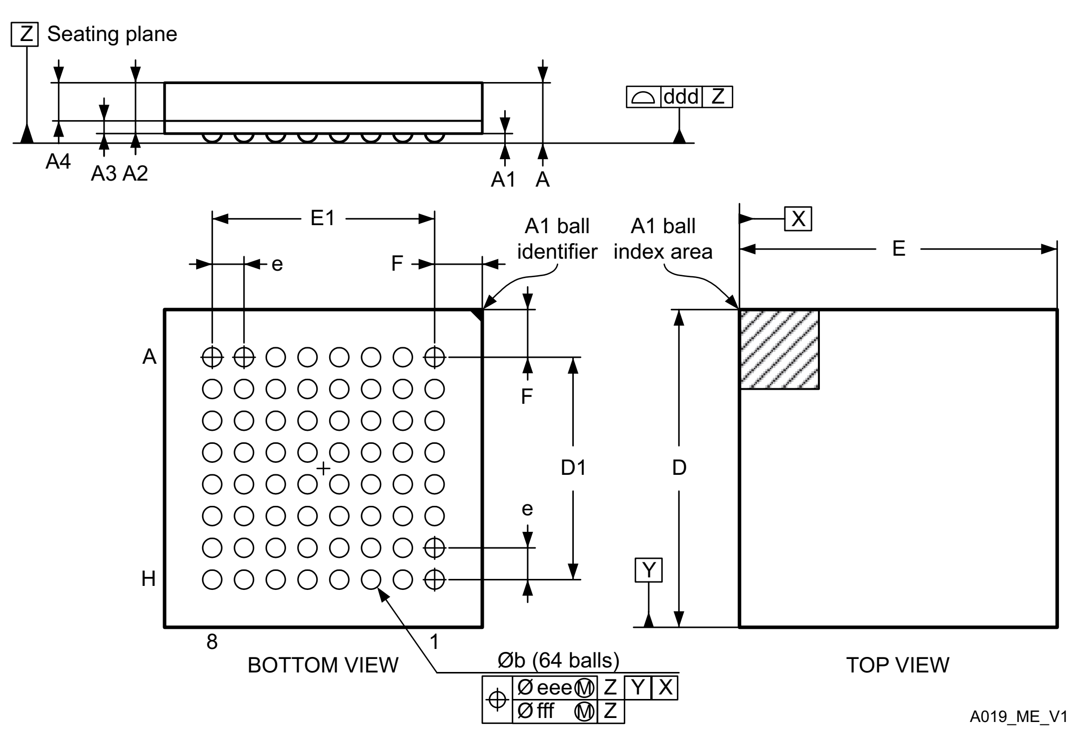
Figure 48. LQFP64 marking (package top view)



1. Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

7.4 UFBGA64 package information

Figure 49. UFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch ultra profile fine pitch ball grid array package outline



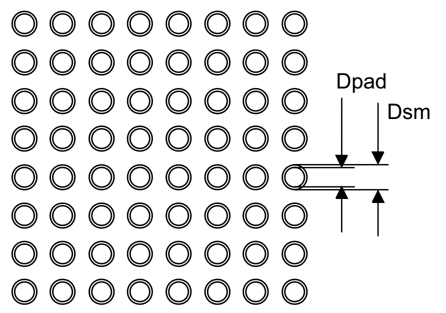
1. Drawing is not to scale.

Table 97. WLCSP64 - 64-ball, 3.357x3.657 mm 0.4 mm pitch wafer level chip scale mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3	-	0.025	-	-	0.0010	-
b	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	3.322	3.357	3.392	0.1308	0.1322	0.1335
E	3.622	3.657	3.692	0.1426	0.1440	0.1454
e	-	0.400	-	-	0.0157	-
e1	-	2.800	-	-	0.1102	-
e2	-	2.800	-	-	0.1102	-
F	-	0.278	-	-	0.0109	-
G	-	0.428	-	-	0.0169	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 53. WLCSP64 - 64-pin, 3.357x3.657 mm 0.4 mm pitch wafer level chip scale recommended footprint



1. Dimensions are expressed in millimeters.